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DESCRIPTION

The PA assembly uses four RF power transistors to provide rated output power. R213, located on the PA module, is used to adjust the output power over a range of 12 Watts to rated output power. The power control circuit consists of R213, Q215, and Power Control IC (U201). Included in the PA assembly, is a Low Pass Filter/Antenna Switch module used to suppress undesired harmonic frequency components and provide antenna switching for the receiver and the transmitter.

SUPPLY VOLTAGE

Supply voltage for the PA is connected through power leads from the system board to feed through capacitors C297 and C298 on the bottom of the PA assembly (See Schematic Diagram). C297, C298, and C299 prevent RF from getting on the power leads. Diode CR295 will cause the main fuse assembly to blow if the polarity of the power leads is reversed, providing reverse voltage protection for the radio.

The PA assembly is insulated from vehicle ground to permit operation in positive or negative ground vehicles.

NOTE

In positive ground vehicles, A- is "hot" with respect to vehicle ground. Shorting the transmitter PA printed wiring board ground pattern to the radio case may cause one of the in-line fuses to blow.

Centralized metering jack J205 is provided for use with GE Test Set Model 4EX3A11 or Test Kit 4EX8K12. The Test Set meters the Ampl-1 drive (exciter output), power control voltage, PA current and PA voltage.

CIRCUIT ANALYSIS**RF POWER AMPLIFIER ASSEMBLY**

The exciter output is coupled through a 50-ohm RF cable to the PA module input jack J201. The 50-ohm RF input is coupled through a matching network comprised of C206, C207, C208 and W202 to the base of power amplifier Q201.

Part of the RF input is rectified by CR201 and metered at J205-4 through resistor R201. The rectified RF is also applied to the power control IC (U201).

Collector voltage for Q201 is applied direct from the DC power input through collector stabilizing network R205 and L202 and collector feed network L203 and C210.

The 500 milliwatt, 50-ohm output of Q201 is coupled to the base of a second power amplifier Q202 through a matching network consisting of T201, C214, C215, C216 and L204.

Collector voltage to Q202 is controlled by power control IC (U201), Q215 and R213 and is applied through a collector stabilizing network L206 and R206 and collector feed network L205 and C218.

The 6 Watt, 50-ohm output of Q202 is coupled to the base of Driver Amplifier

Q203 through C219 and the matching network of T202, C222, C224, C225 and L207. The collector voltage to Q203 is coupled through collector stabilizing network L209 and R214 and collector feed network L208 and C228.

The 20 Watt output of Q203 is coupled through an impedance matching network (C229, C230, C233 and T203) that matches the output impedance of Q203 to the input impedance of power amplifier Q204 through a 50-ohm micro strip (W204) and input impedance matching network T204, C234, C235 and C236.

The collector voltage for Q204 is coupled through collector stabilizing network L212 and R208 and collector feed network C239 and L211. Supply voltage is measured in position F on the 15 volt range with the polarity switch in the (-) position (read as 15 Volts full scale).

Collector current for Q204 is metered across taped manganin resistor R212. The reading taken in position F on the 15 Volt scale with the High Sensitivity button pressed and read as 0-15 amperes full scale.

Following power amplifier Q204 to the 50-ohm input of the Low Pass Filter Module through 50-ohm micro strip W205 and a 50-ohm cable W218.

The input to the Low Pass Filter to the antenna switch K201 is coupled through the 50-ohm micro strip W4280. The output is applied to the antenna at J203.

WARNING

The RF Power Transistor used in the transmitter contains Beryllium Oxide, a TOXIC substance. If the ceramic or other encapsulation is opened, crushed, broken or abraded, the dust may be hazardous if inhaled. Use care in replacing transistors of this type.

POWER CONTROL CIRCUIT

The Power Control Circuit, located on the PA module, consists of CR201, Power Control IC (U201), RT201, Q215 and R213.

When the transmitter is keyed, rectified RF from CR201 is applied to Switch Q1 of Power Control IC (U201), turning it on (See Figure 1). Turning on Q1 turns on

voltage regulator Q2, supplying a constant voltage via Pin 14 to Power Adjust potentiometer R213. R213 through Pin 12 connect to the base of Q5. Q5, Q6 and Q215 operate as an amplifier chain to supply voltage to the collector of Q202 (Ampl-2). The setting of R213 determines the voltage applied to the base of Q5. The higher the voltage at the base of Q5, the harder the amplifiers conduct, supplying more collector voltage to Q202. The lower the voltage at the base of Q5, the less collector voltage is supplied to Q202. Reducing the supply voltage to Q202 reduces the drive to Q203 and Q204, thereby reducing the power output of the PA. The power output can be adjusted by R213 from 12 Watts to rated power output.

Temperature protection is provided by Q3, Q4 in IC U201 and thermistor RT201 which is mounted on the PA heatsink. Under normal operating conditions, the circuit is inactive (Q3 is on and Q4 is off). When the heatsink temperature reaches approximately 115°C the resistance of RT201 decreases. This increases the base voltage applied to Q3, turning it off. Turning off Q3 allows Q4 to turn on, decreasing the voltage at Power Adjust potentiometer R213. This reduces the base voltage to Q5 which causes Q6 and Q215 to conduct less, reducing the collector voltage to Q202 (Ampl-2). This reduces the transmitter output power, keeping the heatsink at a maximum of approximately 115°C. When the heatsink temperature decreases below 115°C, the temperature control circuit turns off, allowing the normal transmitter power output.

ANTENNA MATCHING UNIT

The Antenna Matching Unit is used only in continuous duty duplex stations to optimize impedance matching between the power amplifier and the load. It consists of a Pi network (C2-C5 and L1) and a reverse directional coupler. RF from the low pass filter is applied to the Pi network through the reverse directional coupler and then to the duplexer load. The reverse directional coupler permits monitoring the reflected power by connecting a DC voltmeter across TP1 (+) and ground (-). C2 and C4 are tuned for minimum DC voltage which represents reflected Power. L1 may also be pushed toward or away from the filter cover wall to further reduce the DC voltage. C2, C4, and L1 should be alternately tuned until an absolute minimum voltage reading is obtained. The residual voltage reading after tuning may vary from one transmitter to the next depending on output power level, operating frequency, and the load.

GENERAL ELECTRIC COMPANY • MOBILE COMMUNICATIONS DIVISION
WORLD HEADQUARTERS • LYNCHBURG, VIRGINIA 24502 U.S.A.

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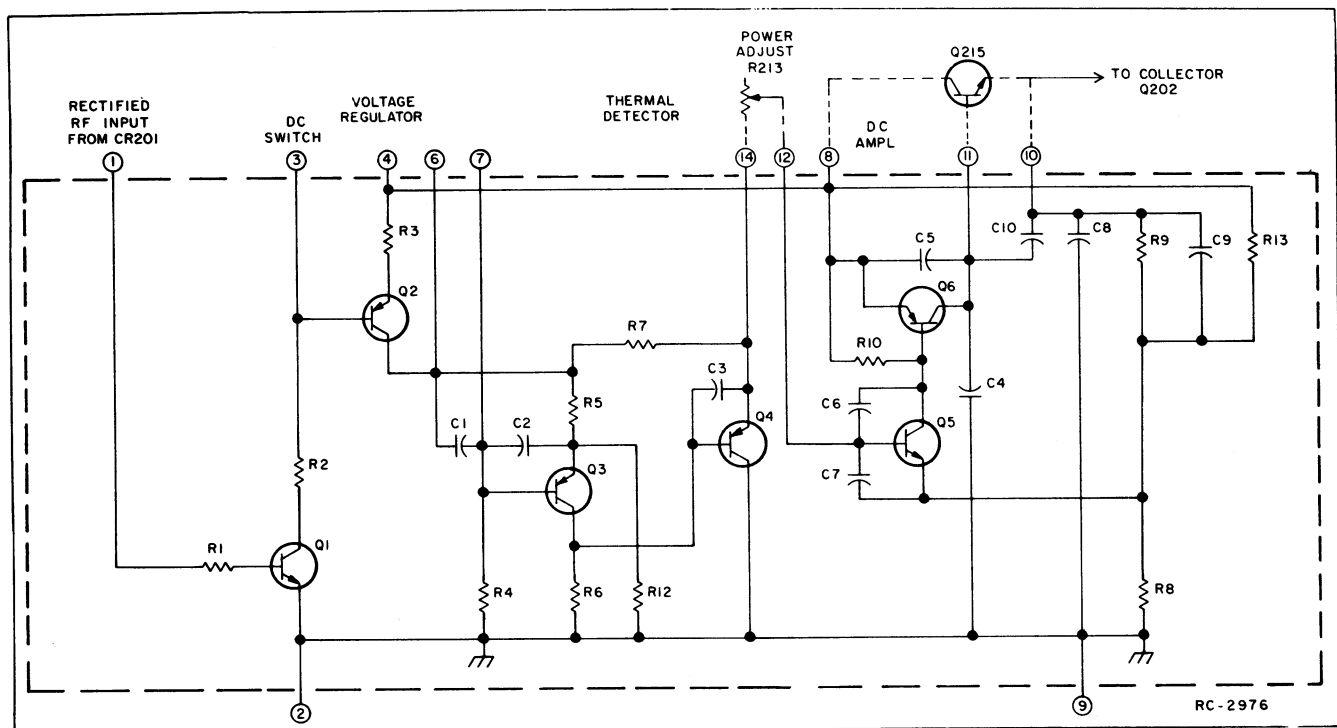
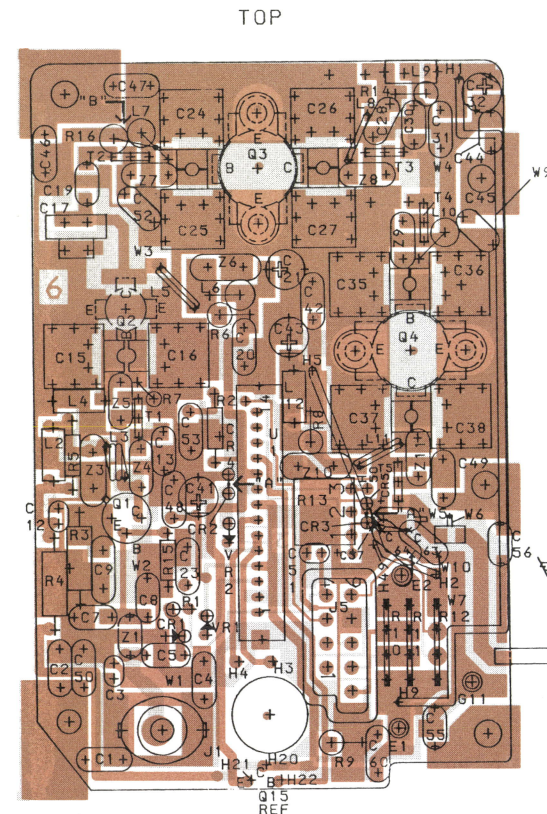
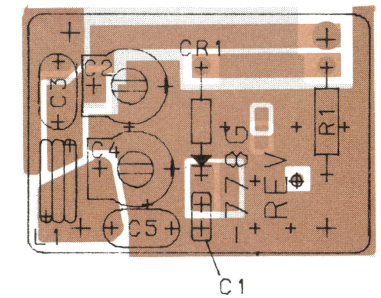


Figure 1 - Power Control IC - U201

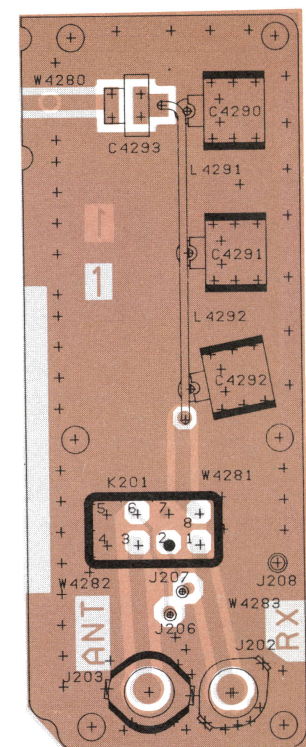
40 WATT PA MODULE



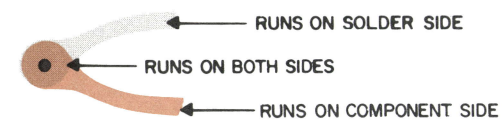
- ### ANTENNA MATCHING (DUPLEX STATIONS) UNIT



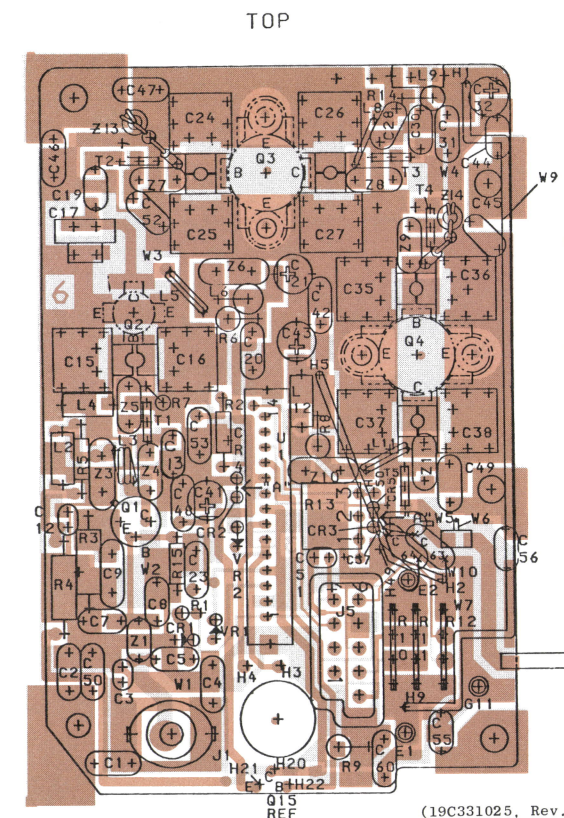
MOBILE & STATION FILTER BOARD



- ## DUPLEX STATION FILTER BOARD



40 WATT PA MODULE

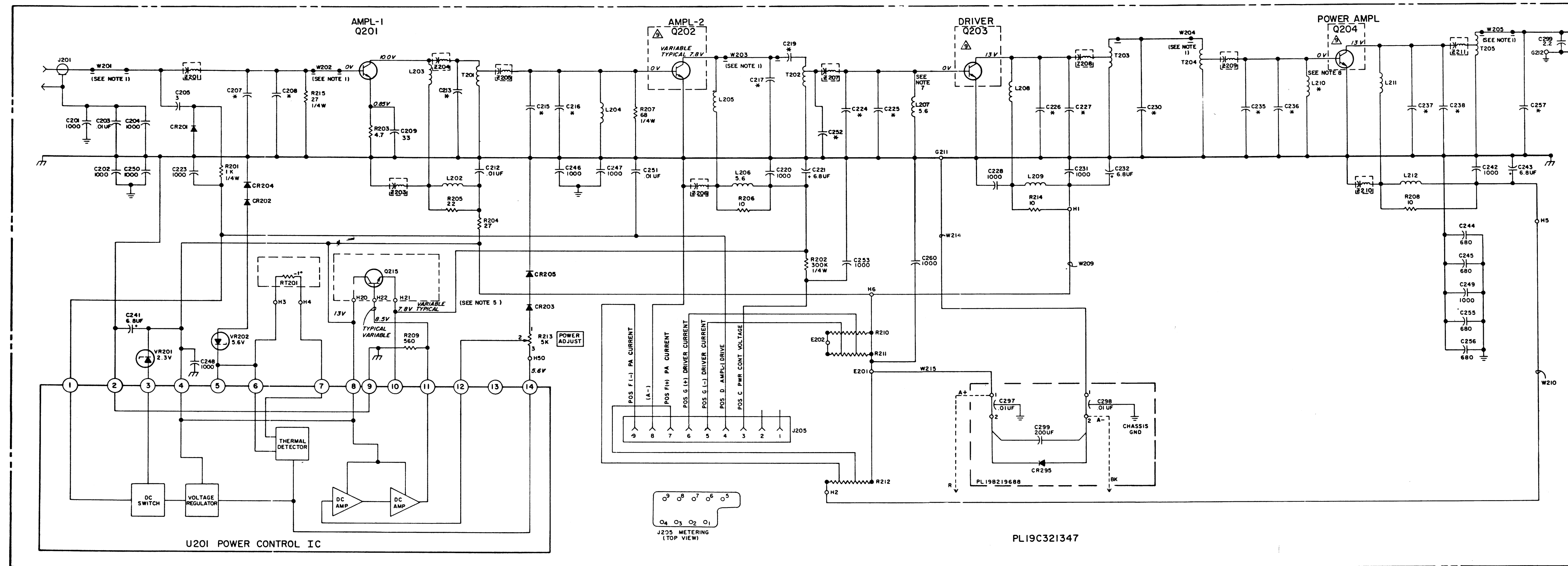


-
- REF
- CR2
CR3
- REF
- CR4
CR5
- .450 MAX.
- VIEW "A"

(19C331025, Rev. 2)
(19B226633, Sh. 1, Rev. 6)
(19B226633, Sh. 2, Rev. 3)

(19D424207, Rev. 3)

4



*COMPONENT VALUES AS FOLLOWS

COMP IDENT	LL 406-450 MHZ	L 450-470 MHZ	M 470-494 MHZ	H 494-512 MHZ
C207	8	9	7	6
C208	8			
C213	5			
C215	47	47	43	43
C216	51	43	43	39
C217	18	16	15	13
C219	680	680	680	680
C224	41	35	35	32
C225	43	35	33	32
C226	47	43	37	35
C227	43	37	37	35
C228	47	35	33	33
C230	7		4	3
C235	47	37	35	33
C237	47	39	37	35
C238	47	43	43	39
C252	9	7	4	3
C257	5			
C4290	10	9	9	9
C4291	20	18	18	18
C4292	13	12	12	12
L210	15	5.6	5.6	5.6
Z203	X	X	X	X
Z204	X	X	X	X
Z205	X	X	X	X
Z207	X	X	X	X
Z208	X	X	X	X
Z209	X	X	X	X
Z210	X	X	X	X
Z211	X	X	X	X
Z213	X			
Z214	X			

PA ASSEMBLY	REV LTR	HEAT SINK ASM	REV LTR
PL19D424888G5	A	PL19B219688G7	
PL19D424888G6	B	PL19B219688G7	
PL19D424888G7	A	PL19B219688G7	
PL19D424888G8	A	PL19B219688G7	
PL19D424888G35	A	PL19B219688G7	
PL19D424888G22	A	PL19B219688G9	
PL19D424888G23	B	PL19B219688G9	
PL19D424888G24	A	PL19B219688G9	
PL19D424888G25	A	PL19B219688G9	
PL19D424888G36		PL19B219688G9	

40 WATT MODULE	REV LTR	FILTER MODULE	REV LTR	FREQUENCY
PL19C32134765	M	PL19C32702461		406-420 MHZ
PL19C32134766	M	PL19C32702462		450-470 MHZ
PL19C32134767	H	PL19C32702462		470-494 MHZ
PL19C32134768	H	PL19C32702462		494-512 MHZ
PL19C32134769	F	PL19C32702461		420-450 MHZ
PL19C32134765	N	PL19C32702461		406-420 MHZ
PL19C32134766	N	PL19C32702462		450-470 MHZ
PL19C32134767	N	PL19C32702462		470-494 MHZ
PL19C32134768	H	PL19C32702462		494-512 MHZ
PL19C32134769	F	PL19C32702461		420-450 MHZ

VOLTAGE READINGS

VOLTAGE READINGS ARE TYPICAL READINGS MADE WITH TRANSMITTER KEYED, AND MEASURED WITH A 20,000 OHMS-PER-VOLT METER WITH REFERENCE TO A- AND NOT CHASSIS GROUND. AN RF CHOKE (25-50 MICROHENRYS) IS USED IN THE HOT METER LEAD TO AVOID DETUNING RF CIRCUITS. NOTE: READINGS AT Q202 COLLECTOR AND IN THE POWER CONTROL CIRCUIT WERE TAKEN WITH THE TRANSMITTER ADJUSTED FOR 40 WATTS OUTPUT. THESE READINGS WILL VARY DEPENDING ON THE SETTING OF POWER ADJUST CONTROL R213.

NOTES

1. MICROSTRIP PART OF PWB.
2. ALL COMPONENTS MARKED WITH (H) ASTERISK, SEE COMPONENT VALUE TABLE.
3. // INDICATES A-
4. ⊕ INDICATES VEHICLE GROUND.
5. R216 USED ONLY IN 450-470MHZ RANGE.
6. C252 NOT USED IN PL19C32134769.

SCHEMATIC DIAGRAM

40 WATT POWER AMPLIFIER

PARTS LIST			SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION			
LBI30214H			C207L*	19A116656P9J0	Ceramic disc: 9 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM.	C215L	19A700131P47	Metallized teflon: 47 pF ±2%, 250 VDCW.	C229M*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Deleted in G7 by REV H.	C238H*	19A700131P39	Metallized teflon: 39 pF ±2%, 250 VDCW.	C257L*	19A134100P20	Ceramic disc: 2.2 pF ±0.1 pF, temp coef 0 ±120 PPM. Deleted by REV B.	R205	19A700106P23	Composition: 22 ohms ±5%, 1/4 w.	Z205M*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G7 by REV H.
400-512 MHz, 40 WATT POWER AMPLIFIER 19D42488G5-G8, G35 ("M" SERIES MOBILE, INT. DUTY STATION) 19D42488G22-G25, G36 ("E" SERIES MOBILE)			19A116656P6J0	In REV D & earlier: Ceramic disc: 6 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM.	C215M	19A700131P43	Metallized teflon: 43 pF ±2%, 250 VDCW.	C229H*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Deleted in G8 by REV H.	C238M*	19A116952P33	Metallized teflon: 33 pF ±2%, 250 VDCW.	C257M*	19A134100P19	Ceramic disc: 1 pF ±0.1 pF, temp coef 0 ±250 PPM. Deleted by REV B.	R206	19A700113P15	Composition: 10 ohms ±5%, 1/2 w.	Z205H*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G8 by REV H.	
			C207M*	19A116656P7J0	Ceramic disc: 7 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM.	C215H	19A700131P43	Metallized teflon: 43 pF ±2%, 250 VDCW.	C239*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Deleted from G5 by REV H.	C238L*	7489162P13	Silver mica: 27 pF ±5%, 500 VDCW; sim. to Sprague Type 118. Added to G5 by REV H. Deleted in G5 by REV L. Deleted in G9 by REV D.	C257H*	19A134100P19	Ceramic disc: 1 pF ±0.1 pF, temp coef 0 ±250 PPM. Deleted by REV B.	R207	19A700106P35	Composition: 68 ohms ±5%, 1/4 w.	Z206*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G8 by REV H.
			19A116656P6J0	In REV E & earlier: Ceramic disc: 6 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM.	C216L	19A700131P51	Metallized teflon: 51 pF ±2%, 250 VDCW, temp coef -130 PPM.	C239LL*	19A116656P7J0	Ceramic disc: 7 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM.	C260	19A116655P20	Ceramic disc: 1000 pF ±10%, 1000 VDCW; sim to RMC Type JF Discap.	C262*	19A116114P2044	Ceramic: 27 pF ±5%, 100 VDCW; temp coef -80 PPM. Added to G6 by REV F. Deleted by REV G.	R208	19A700113P15	Composition: 10 ohms ±5%, 1/2 w.	Z207*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G7, G8 by REV H.	
			C207H	19A116656P6J0	Ceramic disc: 6 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM.	C216M	19A700131P43	Metallized teflon: 43 pF ±2%, 250 VDCW.	C240L*	19A134666P3	Frequency network: selective, 400-500 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:330J:SLAC. Deleted in G5 by REV L. Deleted in G9 by REV D.	C262*	19A116114P2044	Ceramic: 27 pF ±5%, 100 VDCW; temp coef -80 PPM. Added to G6 by REV F. Deleted by REV G.	R209	19A700113P57	Composition: 560 ohms ±5%, 1/2 w.	Z207LL*	19A134666P3	Frequency network: selective, 400-500 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:330J:SLAC. Added to G6 by REV L.			
			C208LL	19A116656P8J0	Ceramic disc: 8 pF ±0.5 pF, 500 VDCW; temp coef 0 PPM.	C216H	19A700131P39	Metallized teflon: 39 pF ±2%, 250 VDCW.	C240L*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Deleted in G6 by REV K.	C263*	19A116655P20	Ceramic disc: 1000 pF ±10%, 1000 VDCW; sim to RMC Type JF Discap.	R210	19A700113P15	Composition: 10 ohms ±5%, 1/2 w.	Z207M*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G7 by REV H.			
			C208L*	19A116656P6J0	Ceramic disc: 6 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM. Deleted by REV E.	C217L	19A116679P16D	Metallized teflon: 16 pF ±0.5 pF, 250 VDCW.	C240M*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Deleted in G6 by REV K.	C264*	19A116655P20	Ceramic disc: 1000 pF ±10%, 1000 VDCW; sim to RMC Type JF Discap.	R211	19A700113P15	Composition: 27 ohms ±5%, 1/4 w.	Z207H*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G7 by REV H.			
			C208M*	19A116656P6J0	Ceramic disc: 6 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM.	C217H	19A116679P15D	Metallized teflon: 15 pF ±0.5 pF, 250 VDCW.	C240H*	19A116656P3J0	Ceramic disc: 3 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM.	CR201	19A116052P1	Silicon, hot carrier: Pwd drop .350 volts max.	R212	19A700113P15	Composition: 10 ohms ±5%, 1/2 w.	Z207M*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G7 by REV H.			
			C208H*	19A116656P6J0	Ceramic disc: 6 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM. Deleted by REV F.	C218*	19A134666P1	Frequency network: selective, 470-630 MHz res. thru TC501:NPO:240J:SLAC. Deleted in G5 by REV L. Deleted in G6 by REV K. Deleted in G7, G8 by REV H. Deleted in G9 by REV D.	C241	19A116655P20	Ceramic disc: 1000 pF ±10%, 1000 VDCW; sim to RMC Type JF Discap.	CR202	19A115250P1	Silicon, fast recovery, 225 mA, 50 PIV.	T201 thru T205	19A130446G1	Coll.	Z207H*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G8 by REV H.			
			C209*	19A116656P3J3J0	Ceramic disc: 33 pF ±5%, 500 VDCW, temp coef 0 PPM. Added to G5 by REV G, G6 by REV E, G7 & G8 by REV F.	C219*	19A116655P18	Ceramic disc: 680 pF ±10%, 1000 VDCW; sim to RMC Type JF Discap. Deleted in G6 by REV J. Added to G6 by REV M.	C242	19A134100P20	Ceramic disc: 2.2 pF ±0.1 pF, temp coef 0 ±120 PPM. Deleted by REV B.	C243	19A134202P15	Tantalum: 6.8 uF ±20%, 35 VDCW.	E201 and E202	19A134263P1	Contact, electrical: sim to Selectro 229-1082-00-0-590.	Z207H*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G8 by REV H.			
			C209LL*	7489162P15	Silver mica: 33 pF ±5%, 500 VDCW; sim. to Sprague Type 118. Deleted by REV C. Added by REV D. Deleted by REV G.	C219L*	19A116656P24J0	Ceramic disc: 24 pF ±5%, 500 VDCW, temp coef 0 PPM. Added to G6 by REV J. Deleted in G6 by REV M.	C243	19A134100P20	Ceramic disc: 2.2 pF ±0.1 pF, temp coef 0 ±120 PPM. Deleted by REV B.	C244 and C245	19A134202P15	Tantalum: 6.8 uF ±20%, 35 VDCW.	G211	19A134263P1	Contact, electrical: sim to Selectro 229-1082-00-0-590.	Z208L*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G8 by REV K.			
			C209L*	7489162P11	Silver mica: 22 pF ±5%, 500 VDCW; sim to Sprague Type 118. Deleted by REV C.	C220	19A116655P20	Ceramic disc: 1000 pF ±10%, 1000 VDCW; sim to RMC Type JF Discap.	C244	19A116655P18	Ceramic disc: 680 pF ±10%, 1000 VDCW; sim to RMC Type JF Discap.	CR203	19A116655P20	Ceramic disc: 1000 pF ±10%, 1000 VDCW; sim to RMC Type JF Discap.	VR201	4036887P1	Zener: 500 mW, 2.3 v. nominal.	Z208M*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G7 by REV H.			
			C209M*	7489162P11	Silver mica: 22 pF ±5%, 500 VDCW; sim to Sprague Type 118. Deleted by REV C.	C221	19B209723P4	Tantalum: 6.8 uF ±20%, 35 VDCW.	C246 thru C250	19A116655P20	Ceramic disc: 1000 pF ±10%, 1000 VDCW; sim to RMC Type JF Discap.	J201	19A700049P2	Connector, receptacle: 500 VDCW maximum; sim to NTF-1058.	VR202	4036887P5	Zener: 500 mW, 5.4 v. nominal.	Z208H*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G7 by REV H.			
			C209H*	7489162P13	Silver mica: 27 pF ±5%, 500 VDCW; sim. to Sprague Type 118. Deleted by REV C.	C222LL*	19A134666P3	Frequency network: selective, 400-500 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:330J:SLAC. Deleted in G5 by REV L. Deleted in G6 by REV D.	C251	19A116192P1	Ceramic: 0.01 uF ±20%, 50 VDCW; sim to Erie 8121 SPECIAL.	J205	19B219374G1	Connector: 9 contacts.	W201 thru W205	19A700049P2	(Part of printed board 19D423005P1).	Z208H*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G8 by REV H.			
			C210LL*	19A134666P3	Frequency network: selective, 400-500 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:330J:SLAC. Deleted in G5 by REV L. Deleted in G6 by REV D.	C222L*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Deleted in G6 by REV K.	C252LL*	19A116656P5J0	Ceramic disc: 5 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM.	L202	19A701091G1	Coil.	W206	19A701093P1	Strap.	Z209LL*	19A134666P3	Frequency network: selective, 400-500 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:330J:SLAC. Added to G5 by REV L.			
			C210L*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Deleted in G6 by REV K.	C222M*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Deleted in G7 by REV H.	19A116952P43	Metallized teflon: 43 pF ±2%, 250 VDCW.	19A116656P9J0	Ceramic disc: 9 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM.	L203	19A129774P1	Coil.	W209	19B226733G1	Jumper.	Z209M*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G7 by REV H.		
			C210M*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Deleted in G7 by REV H.	C222H*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Deleted in G8 by REV H.	19A116656P30	Metallized teflon: 30 pF ±2%, 250 VDCW.	19A116656P9J0	Ceramic disc: 9 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM.	L204	19A701091G1	Coil.	W210	19B226734G1	Jumper.	Z209H*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G8 by REV H.		
			C210H*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Deleted in G8 by REV H.	C223	19A116655P20	Ceramic disc: 1000 pF ±10%, 1000 VDCW; sim to RMC Type JF Discap.	C234L*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Deleted in G6 by REV K.	19A116952P43	Metallized teflon: 43 pF ±2%, 250 VDCW.	L206	19A700000P120	Coil, RF: 5.6 uH ±10%; sim to Jeffers 4422-1K.	Z201*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 50				

SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION
		----- RESISTORS -----			
R1	19A700106P15	Composition: 10 ohms $\pm 5\%$, 1/4 w. LOW PASS FILTER 19C327024G1 406-450 MHz (LL) 19C327024G2 450-512 MHz (H) (Added to 19D424888 by REV A)	J206 and J207		(Part of K201).
		----- RELAYS -----	J208	4033513P4	Contact, electrical: sim to Bead Chain L93-3.
C4290LL	19A700014P4	Metallized teflon: 10 pF $\pm 5\%$, 250 VDCW.	K201	19A116722P1	Hermetic sealed: 125 ohms $\pm 20\%$, 1 form C contact, 9.6 to 15.8 VDC (over the temp range indicated). (Includes J208 & J207).
C4290H	19A7000131P9	Metallized teflon: 9 pF ± 0.5 pF, 250 VDCW.			----- CABLES -----
C4291LL	19A700131P20	Metallized teflon: 20 pF ± 0.5 pF, 100 VDCW.	W4280 thru W4283		(Part of printed board 19D423316P1).
C4291H	19A700131P18	Metallized teflon: 18 pF ± 0.5 pF, 250 VDCW.			HEAT SINK 19B219688G7 "M" SERIES 19B219688G19 "E" SERIES
C4292LL	19A700131P13	Metallized teflon: 13 pF ± 0.5 pF, 250 VDCW.			----- CAPACITORS -----
C4292H	19A700131P12	Teflon: 12 pF ± 0.5 pF, 250 VDCW.	C297 and C298		
C4293	19A700015P37	Teflon/Mica: 220 pF $\pm 5\%$, 250 VDCW.	C299	19A115680P10	Electrolytic: 220 uF $\pm 150\%$ -10%, 18 VDCW; sim to Mallory Type TTX.
		----- INDUCTORS -----	CR295	19A116783P1	Rectifier, silicon: 100 VDC blocking, 6 amps.
L4291LL	19B226709G2	Jumper. (Includes L4292LL).			----- MISCELLANEOUS -----
L4291H	19B226709G1	Jumper. (Includes L4292H).	5492178P2		Washer, spring tension: sim to Wallace Barnes 375-20. (Used with Q202).
L4292LL		(Part of L4291LL).	19A702182P1		Spacer. (Used with Q202).
L4292H		(Part of L4291H).	19A702782P5		Nut, hex, brass: No. 8-32. (Used with Q202).
		----- JACKS AND RECEPTACLES -----	N44P9010C6		Machine screw: No. 4-40 x 5/8. (Used with Q203, Q204).
J202 and J203	19A700049P2	Connector, receptacle; 500 VDCW maximum; sim to NTTF-1058.	19A700068P1		Insulator, bushing. (Used with Q215).
J206 and J207	19A134263P2	Contact, electrical: sim to Selectro 229-1071.	19A116023P1		Insulator, plate. (Used with Q215).
J208	4033513P4	Contact, electrical: sim to Bead Chain L93-3.	19B201074P312		Tap screw, Phillips POZIDRIVE: No. 6-32 x 3/4. (Secures Mobile Filter Assembly).
		----- RELAYS -----	19B201074P306		Tap screw, Phillips POZIDRIVE: No. 6-32 x 3/8. (Secures Filter Board).
K201	19A700061P1	Hermetic sealed: 180 to 341 ohms coil res, 8-16.3 VDC; sim to GE 38A1760A2, CP Clare HPW-1201558, or Potter-Brumfield HCM6160.	19C321441P1		Insulator. (Located under 40 watt Module).
		----- CABLES -----	19D416732G7		Heat sink. ("M" SERIES).
W4280 thru W4283		(Part of printed board 19D423812P1).	19D417105G7		Heat sink. ("E" SERIES).
		LOW PASS FILTER MODULE 19C321424G1 406-450 MHz (LL) 19C321424G2 450-512 MHz (H) (Deleted on 19D424888 by REV A)	19A129639P1		Cover, Heat Sink Assembly. ("E" SERIES).
		----- CAPACITORS -----	19A701332P4		Insulator, washer: nylon. (Used with Q201).
C4280LL	19A700014P4	Metallized teflon: 10 pF $\pm 5\%$, 250 VDCW.	N80P9006C6		Machine screw: No. 4-40 x 3/8. (Secures Q215 in Mobile).
C4280H	19A700131P9	Metallized teflon: 9 pF ± 0.5 pF, 250 VDCW.	714122502		Hex nut: No. 4-40. (Secures Q215).
C4281LL	19A700131P20	Metallized teflon: 20 pF ± 0.5 pF, 100 VDCW.	N403P35C6		Washer, steel: No. 4. (Secures Q215).
C4281H	19A700131P18	Metallized teflon: 18 pF ± 0.5 pF, 250 VDCW.	N80P13010C6		Machine screw: No. 6-32 x 5/8. (Secures Mobile 40 Watt Module).
C4282LL	19A700131P13	Metallized teflon: 13 pF ± 0.5 pF, 250 VDCW.			
C4282H	19A700131P12	Teflon: 12 pF ± 0.5 pF, 250 VDCW.			
C4283LL	19A700015P37	Teflon/Mica: 220 pF $\pm 5\%$, 250 VDCW.			
C4283H	19A700015P37	Teflon/Mica: 220 pF $\pm 5\%$, 250 VDCW.			
		----- INDUCTORS -----			
L4281	19B226709G1	Jumper. (450-512 MHz).			
L4282	19B226709G2	Jumper. (406-450 MHz).			
		----- JACKS AND RECEPTACLES -----			
J202 and J203	19A700049P2	Connector, receptacle; 500 VDCW maximum; sim to NTTF-1058.			

PRODUCTION CHANGES

Changes in the equipment to improve performance or to simplify circuits are identified by a "Revision Letter," which is stamped after the model number of the unit. The revision stamped on the unit includes all previous revisions. Refer to the Parts List for descriptions of parts affected by these revisions.

REV. A - PA Assembly 19D42488G5-G8, G22-G23
To incorporate new low-pass filter. Deleted 19C321424. Added 19C327024.

REV. A - 40 Watt Module 19C321347G5-G8
To improve power output at cold temperatures. Added CR204 & CR205.

REV. B - 40 Watt Module 19C321347G5-G8
To improve operation.
In 19C321347G5: deleted C213 and changed C252LLB.
In 19C321347G6: deleted C233L, C257L and added C252LLB.
In 19C321347G7: deleted C237H and added C252HB.
In 19C321347G8: deleted C233H, C257H and added C252HB.

REV. C - 40 Watt Module 19C321347G5-G8
To improve operation. Deleted C209 and R203. Changed R204.

REV. D - 40 Watt Module 19C321347G5
To improve operation. Added C209 and R203.

REV. E - 40 Watt Module 19C321347G5
To improve station operation. Added C213.

REV. D - 40 Watt Module 19C321347G6-G8
To improve operation. Changed C206.

REV. F - 40 Watt Module 19C321347G5
To improve operation. Changed C206.

REV. E - 40 Watt Module 19C321347G7, G8
To improve RF output and efficiency. Changed C237 (Group 8) and C238 (Groups 7 & 8).

REV. G - 40 Watt Module 19C321347G5
REV. E - 40 Watt Module 19C321347G6
REV. F - 40 Watt Module 19C321347G7, G8
To decrease spurious outputs. Changed C207L, M and C209. Deleted C208L, M, H. Added R203 to Groups 6, 7 and 8.

REV. H - 40 Watt Module 19C321347G5
To increase output at 406 MHz. Changed C252LLB. Deleted C239. Added C239LLB.

REV. J - To improve stability. Changed Q203LL.

REV. F - 40 Watt Module 19C321347G6
To improve stability. Added R216 and C262.

REV. G - To improve operation. Deleted C262.

REV. A - 40 Watt Module 19C321347G9
To improve operation. Added C240LL.

REV. B - To improve stability. Changed Q203LL.

REV. K - 40 Watt Module 19C321347G5
REV. H - 40 Watt Module 19C321347G6
REV. G - 40 Watt Module 19C321347G7
REV. G - 40 Watt Module 19C321347G8
REV. C - 40 Watt Module 19C321347G9
To improve operation of power regulator circuit when used as driver for 100 Watt PA. Added C263 and C264.

REV. J - 40 Watt Module 19C321347G6
To increase output power at low end of 450-470 MHz range. Changed C252.

REV. L - 40 Watt Module 19C321347G5
REV. K - 40 Watt Module 19C321347G6
REV. H - 40 Watt Module 19C321347G7
REV. H - 40 Watt Module 19C321347G8
REV. D - 40 Watt Module 19C321347G9
To incorporate new nomenclature for frequency selection networks.

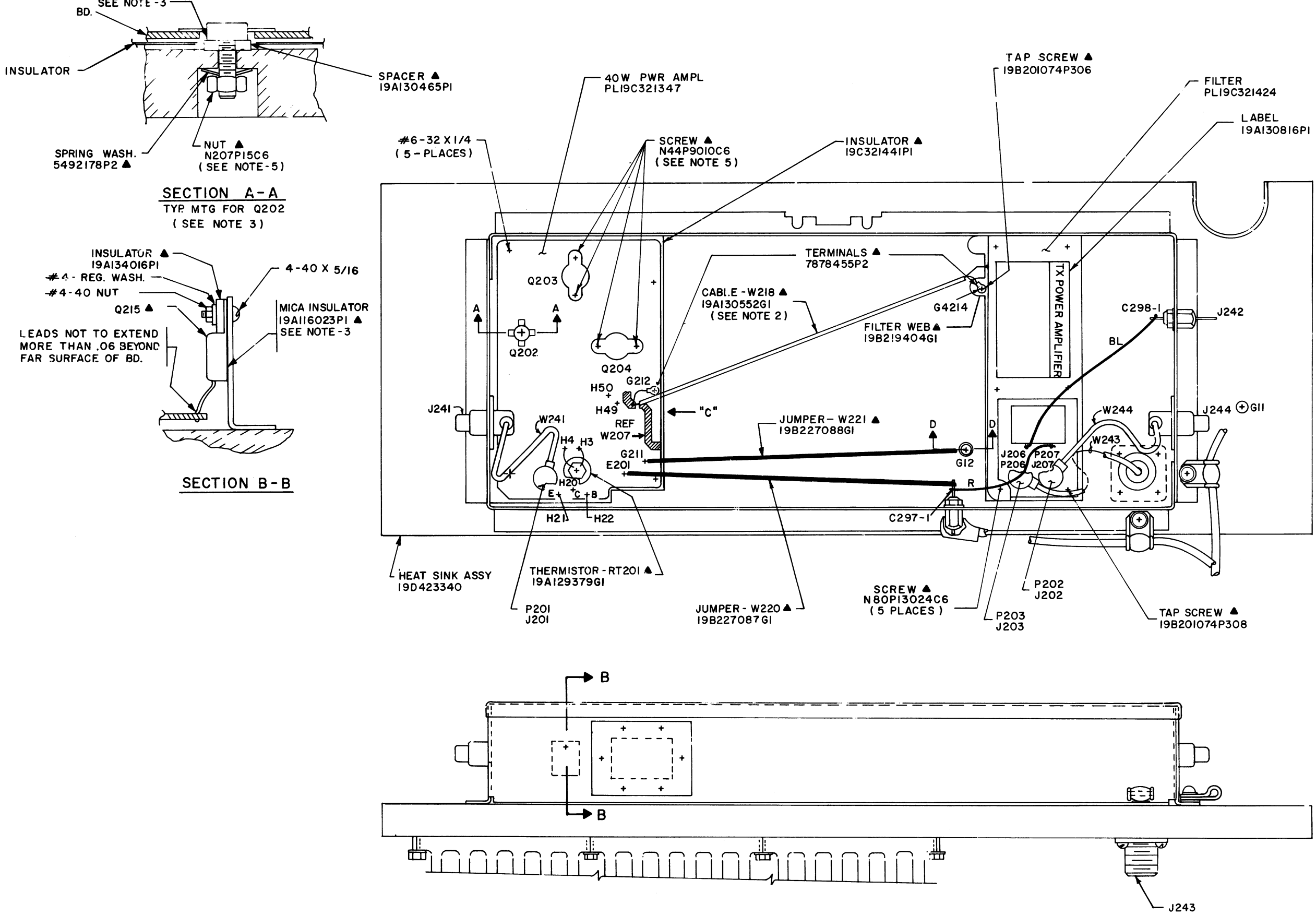
REV. B - PA Assembly 19D42489G6, G23
To improve power output. Added C299.

REV. M - 40-Watt Module 19C321347G5
REV. E - 40-Watt Module 19C321347G9
To improve power output across the board. Deleted C213LL, L207, and L210LL. Added C213 and C214. Changed C257LL, C259LLB (Group 5 only), and Q203LLB.

REV. N - 40-Watt Module 19C321347G5
REV. F - 40-Watt Module 19C321347G9
To improve power output. Changed C230LL, C235LL, C236LL and C257LL. Added C219LL.

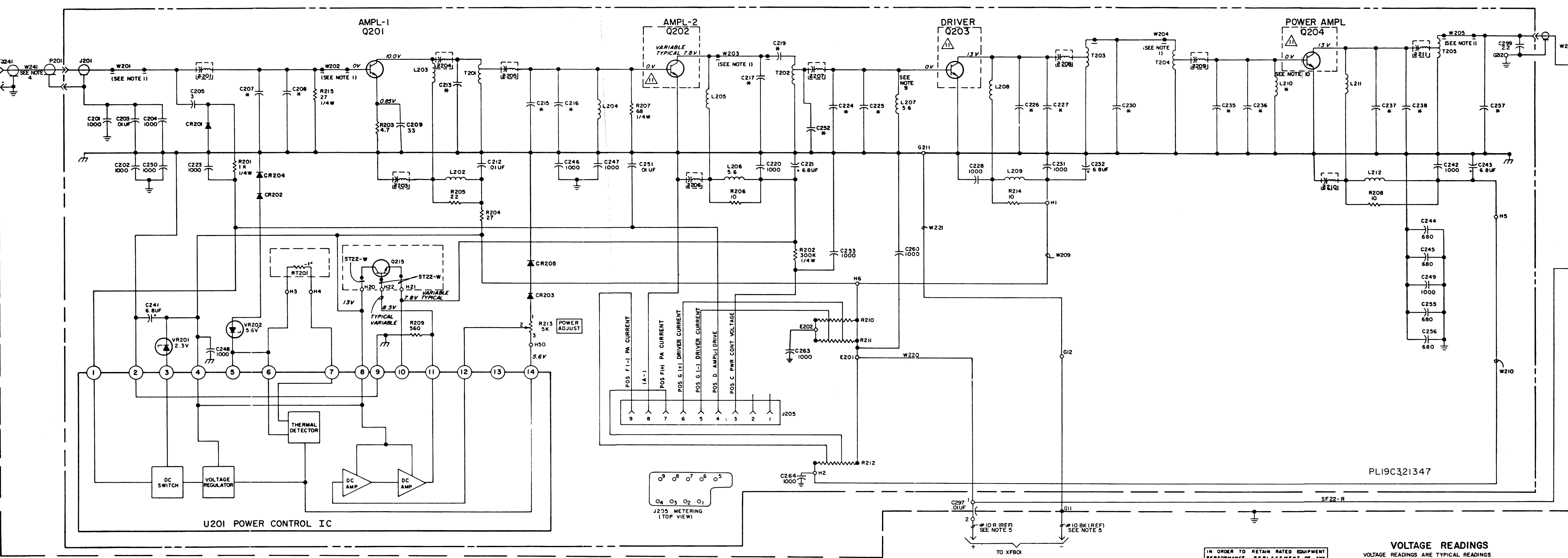
REV. L - 40-Watt Module 19C321347G6
To increase power output. Changed C252LB and C237. Deleted R216 and C230.

REV. M - 40-Watt Module 19C321347G6
To improve power output over the 450-470 MHz range. Changed C219L and C250L.



SCHEMATIC DIAGRAM

CONTINUOUS DUTY STATION POWER AMPLIFIER
AND ANTENNA MATCHING UNIT



IN ORDER TO RETAIN RATED EQUIPMENT
PERFORMANCE, REPLACEMENT OF ANY
SERVICE PART SHOULD BE MADE ONLY WITH
A COMPONENT HAVING THE SPECIFICATIONS
SHOWN ON THE PARTS LIST FOR THAT PART.

VOLTAGE READINGS

VOLTAGE READINGS ARE TYPICAL READINGS
MADE WITH TRANSMITTER KEYED AND MEASURED
WITH A 20,000 OHMS-PER-VOLT METER WITH
REFERENCE TO A- AND NOT CHASSIS GROUND AN RF
CHOKE (25-50 MICROHENRYS) IS USED IN THE HOT
METER LEAD TO AVOID DETUNING RF CIRCUITS
NOTE READINGS AT Q202 COLLECTOR AND IN THE
POWER CONTROL CIRCUIT WERE TAKEN WITH THE
TRANSMITTER ADJUSTED FOR 40 WATT OUTPUT
THESE READINGS WILL VARY DEPENDING ON THE
SETTING OF POWER ADJUST CONTROL R213

ALL RESISTORS ARE 1/4 WATT UNLESS
OTHERWISE SPECIFIED AND RESISTOR
VALUES IN OHMS UNLESS FOLLOWED BY
K=1000 OHMS OR MEG=1,000,000 OHMS.
CAPACITOR VALUES IN PICOFARADS (EQUAL
TO MICROMICROFARADS) UNLESS FOLLOWED
BY UF= MICROFARADS. INDUCTANCE VALUES
IN MICROHENRYS UNLESS FOLLOWED BY
MH= MILLIHENRYS OR H=HENRYS

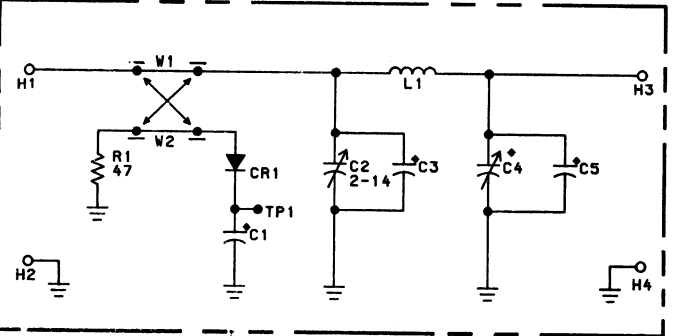
(198622186, Rev. 34)

- NOTES:
1. MICROSTRIP PART OF PWB.
 2. ALL COMPONENTS MARKED WITH (M)
 3. ASTERISK, SEE COMPONENT VALUE TABLE.
 4. * INDICATES A-
 5. ± INDICATES CHASSIS GROUND.
 6. CALLED FOR ON 19D417525.
 7. CALLED FOR ON 19D42895
 8. R218 USED ONLY 40-450-470MHZ RANGE.
 9. C252 NOT USED IN PL19C321347G9
 10. ON PL19C321347G5 DELETE L207 & ADD #213.
 11. ON PL19C321347G9 DELETE L210 & ADD #214
 12. PART OF NEXT LEVEL HIGHER ASM. (PA)

* COMPONENT VALUE CHART			
COMPONENT DESIGNATION	A	B	C
C1	1000	406-470	470
C4	2-14	2-10	
C3	15		
C5	10		

ALL RESISTORS ARE 1/4 WATT UNLESS
OTHERWISE SPECIFIED AND RESISTOR
VALUES IN OHMS UNLESS FOLLOWED BY
K=1000 OHMS OR MEG=1,000,000 OHMS.
CAPACITOR VALUES IN PICOFARADS (EQUAL
TO MICROMICROFARADS) UNLESS FOLLOWED
BY UF= MICROFARADS. INDUCTANCE VALUES
IN MICROHENRYS UNLESS FOLLOWED BY
MH= MILLIHENRYS OR H=HENRYS.

ANTENNA MATCHING UNIT



(198233613, Rev. 1)

* COMPONENT VALUES AS FOLLOWS				
COMP IDENT	LL 406-450 MHZ	L 450-470 MHZ	M 470-494 MHZ	H 494-512 MHZ
C207	8	9	7	6
C208	8			
C213	5			
C215	47	47	43	43
C216	51	43	43	39
C217	18	16	15	13
C219	680	680	680	680
C224	41	35	35	32
C225	43	35	33	32
C226	47	43	37	35
C227	43	37	37	35
C230	7		4	3
C235	47	37	35	33
C236	47	35	33	33
C237	47	39	37	35
C238	47	43	43	39
C252	9	7	4	3
C257	5			
C4290	10	9	9	9
C4291	20	18	18	18
C4292	13	12	12	12
L210	15	5.6	5.6	5.6
#203	X	X	X	X
#204	X	X	X	X
#205	X	X	X	X
#207	X	X	X	X
#208	X	X	X	X
#209	X	X	X	X
#210	X	X	X	X
#211	X	X	X	X
#213	X			
#214	X			

MODEL NO.	REV. LETTER
19C33077801	
19C33077802	
19C33077803	

PARTS LIST			SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION				
LBI30594G																								
406-512 MHz, 40 WATT POWER AMPLIFIER 19D42489G5-G8, G36 (CONTINUOUS DUTY) 19D42489G22-G25, G37 (CONTINUOUS DUTY - DUPLEX)																								
SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION				
C297 and C298	19A116708P1	Ceramic: 0.01 uF ±0 +100%, 500 VDCW, rated 20 amps; sim to Erie 327050X5W0103P.	C204	19A116655P20	Ceramic disc: 1000 pF ±10%, 1000 VDCW; sim to RMC Type JF Discap.	C226L	19A700131P43	Metallized teflon: 43 pF ±2%, 250 VDCW.	C237LL	19A700131P47	Metallized teflon: 47 pF ±2%, 250 VDCW.	C252M*	19A116656P4J0	Ceramic disc: 4 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM. Added by REV B.	L211	19B219457P6	Coil.							
	C299*	19A134100P20	Ceramic disc: 2.2 pF ±0.1 pF, temp coef 0 ±120 PPM. Added to G6 by REV C, G23 by REV D.	C205	19A116656P3J0	Ceramic disc: 3 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM.	C226H	19A700131P37	Metallized teflon: 37 pF ±2%, 250 VDCW.	C237L*	19A700131P39	Metallized teflon: 39 pF ±2%, 250 VDCW.	C252H*	19A116656P3J0	Ceramic disc: 3 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM. Added by REV B.	L212	19A701091G1	Coil.						
	G212 and G213	7878455P2	Solderless terminal.	C206*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Deleted in G5 by REV L. Deleted in G6 by REV K. Deleted in G7, G8 by REV H. Deleted in G9 by REV D.	C226H	19A700131P35	Teflon/mica: 35 pF ±2%, 250 VDCW.				C253	19A116655P20	Ceramic disc: 1000 pF ±10%, 1000 VDCW; sim to RMC Type JF Discap.	Q201	19A134237P1	Silicon, NPN.						
	G4214	7878455P2	Solderless terminal.				C227LL	19A700131P43	Metallized teflon: 43 pF ±2%, 250 VDCW.	C237M	19A700131P37	Metallized teflon: 37 pF ±2%, 250 VDCW.												
J243	5491689P108	Connector/cable: approx. 10 inches long.	C207LL	19A116656P8J0	Ceramic disc: 8 pF ±0.5 pF, 500 VDCW; temp coef 0 PPM.	C214L*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Deleted in G6 by REV K.	C237H*	19A700131P35	Metallized teflon: 37 pF ±2%, 250 VDCW.	C238LL	19A700131P43	Metallized teflon: 43 pF ±2%, 250 VDCW.	C255 and C256	19A116655P18	Ceramic disc: 680 pF ±10%, 1000 VDCW; sim to RMC Type JF Discap.							
						C214M*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Deleted in G7 by REV H.				C238M*	19A700131P43	Metallized teflon: 43 pF ±2%, 250 VDCW.										
	P203		Connector. Includes receptacle and adaptor. (Order separately).	C207M*	19A116656P7J0	Ceramic disc: 7 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM.	C214H*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Deleted in G8 by REV H.															
Q202	19A134164P2	Silicon, NPN; sim to Type 2N5945.	C208LL	19A116656P8J0	Ceramic disc: 8 pF ±0.5 pF, 500 VDCW; temp coef 0 PPM.	C215LL	19A700131P47	Metallized teflon: 47 pF ±2%, 250 VDCW.	C239	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Deleted in G5 by REV L. Deleted in G6 by REV K.	C239LL*	7489162P13	Silver mica: 27 pF ±5%, 500 VDCW; sim. to Sprague Type 118. Added to G5 by REV H. Deleted in G5 by REV L. Deleted in G9 by REV D.	CR201	19A116052P1	Silicon, hot carrier: Fwd drop .350 volts max.							
	Q203LL	19A134239P3	Silicon, NPN.	C208L*	19A116656P6J0	Ceramic disc: 6 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM. Deleted by REV E.	C215M	19A700131P43	Metallized teflon: 43 pF ±2%, 250 VDCW.	C239M*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Deleted in G6 by REV K.												
	Q203M	19A134239P1	Silicon, NPN.	C208H*	19A116656P6J0	Ceramic disc: 6 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM. Deleted by REV F.	C215H	19A700131P43	Metallized teflon: 43 pF ±2%, 250 VDCW.	C240LL*	19A134666P3	Frequency network: selective, 400-500 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:330J:SLAC. Deleted in G5 by REV L. Deleted in G9 by REV D.	C240L*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Deleted in G6 by REV K.	C263*	19A116655P20	Ceramic disc: 1000 pF ±10%, 1000 VDCW; sim to RMC Type JF Discap.	R214	19A700113P15	Composition: 10 ohms ±5%, 1/2 w.			
	Q204LL	19A134242P3	Silicon, NPN.	C208M*	19A116656P6J0	Ceramic disc: 6 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM. Deleted by REV F.	C216LL	19A700131P51	Metallized teflon: 51 pF ±2%, 250 VDCW, temp coef -130 PPM.	C240M*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Deleted in G6 by REV K.												
Q204L	19A134242P3	Silicon, NPN.	C208H*	19A116656P6J0	Ceramic disc: 6 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM. Deleted by REV F.	C216M	19A700131P43	Metallized teflon: 43 pF ±2%, 250 VDCW.	C241	19A134202P15	Tantalum: 6.8 uF ±20%, 35 VDCW.	C241	19A134202P15	Tantalum: 6.8 uF ±20%, 35 VDCW.	CR202 thru CR205	19A115250P1	Silicon, fast recovery, 225 mA, 50 PIV.	T201	19A130446G1	Coil.				
	Q204H	19A134242P4	Silicon, NPN; 50 Watt.	C209*	19A116656P3J30	Ceramic disc: 33 pF ±5%, 500 VDCW, temp coef 0 PPM. Added to G5 by REV G, G6 by REV E, G7 & G8 by REV F.	C217LL	19A116679P18D	Metallized teflon: 18 pF ±0.5 pF, 250 VDCW.	C242	19A116655P20	Ceramic disc: 1000 pF ±10%, 1000 VDCW; sim to RMC Type JF Discap.	C242	19A116655P20	Ceramic disc: 1000 pF ±10%, 1000 VDCW; sim to RMC Type JF Discap.									
	Q215	19A116753P1	Silicon, NPN.	C209M*	19A116656P3J0	Ceramic disc: 33 pF ±5%, 500 VDCW, temp coef 0 PPM. Added to G5 by REV G, G6 by REV E, G7 & G8 by REV F.	C217M	19A116679P15D	Metallized teflon: 15 pF ±0.5 pF, 250 VDCW.	C243	19A134202P15	Tantalum: 6.8 uF ±20%, 35 VDCW.	C243	19A134202P15	Tantalum: 6.8 uF ±20%, 35 VDCW.									
							C217H	19A116679P13D	Metallized teflon: 13 pF ±0.5 pF, 250 VDCW.	C244 and C245	19A116655P18	Ceramic disc: 680 pF ±10%, 1000 VDCW; sim to RMC Type JF Discap.	C244 and C245	19A116655P18	Ceramic disc: 680 pF ±10%, 1000 VDCW; sim to RMC Type JF Discap.									
RT201	19A129379G1	Thermistor: 40K ohms ±20%, color code white; sim to Carborundum Type M0806J-5.	C209H*	19A116656P6J0	Ceramic disc: 6 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM. Deleted by REV F.	C218*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Deleted in G5 by REV L. Deleted in G6 by REV K. Deleted in G7, G8 by REV H. Deleted in G9 by REV D.	C246 thru C250	19A116655P20	Ceramic disc: 1000 pF ±10%, 1000 VDCW; sim to RMC Type JF Discap.	C251	19A116192P1	Ceramic: 0.01 uF ±20%, 50 VDCW; sim to Erie 8121 SPECIAL.	J201	19A700049P2	Connector, receptacle; 500 VDCW maximum; sim to NTTP-1058.							
						C219*	19A116655P18	Ceramic disc: 680 pF ±10%, 1000 VDCW; sim to RMC Type JF Discap. Deleted in G6 by REV M. Added to G6 by REV J. Deleted in G6 by REV M.	C251	19A116192P1	Ceramic: 0.01 uF ±20%, 50 VDCW; sim to Erie 8121 SPECIAL.													
	W218	19A130552G1	Jumper.	C210LL*	19A134666P3	Frequency network: selective, 400-500 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:330J:SLAC. Deleted in G5 by REV L. Deleted in G9 by REV D.	C219L*	19A116656P24J0	Ceramic disc: 24 pF ±5%, 500 VDCW, temp coef 0 PPM. Added to G6 by REV J. Deleted in G6 by REV M.	C252LL*	19A116656P5J0	Ceramic disc: 5 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM.	J205	19B219374G1	Connector: 9 contacts.	W201 thru W205								
	W220	19B227087G1	Jumper: 6 inches long.	C210M*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Deleted in G6 by REV K.	C220	19A116655P20	Ceramic disc: 1000 pF ±10%, 1000 VDCW; sim to RMC Type JF Discap.	C252L*	19A116656P9J0	Ceramic disc: 9 pF ±0.5 pF, 500 VDCW, temp coef 0 PPM.												
W221	19B227088G1	Jumper.	C210H*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Deleted in G7 by REV H.	C221	19B209723P4	Tantalum: 6.8 uF ±20%, 35 VDCW.	C255L*	19A700131P37	Metallized teflon: 37 pF ±2%, 250 VDCW.	C255L*	19A700131P37	Metallized teflon: 37 pF ±2%, 250 VDCW.	L202	19A701091G1	Coil.	W206	19A701093P1	Strap.				
	W243	19A1293126G	Antenna cable: approx 10 inches long. (Includes J243 & P203).	C211LL*	19A134666P3	Frequency network: selective, 400-500 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:330J:SLAC. Deleted in G5 by REV L. Deleted in G9 by REV D.	C222LL*	19A134666P3	Frequency network: selective, 400-500 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:330J:SLAC. Deleted in G5 by REV L. Deleted in G9 by REV D.	C256LL*	19A700131P35	Teflon/mica: 35 pF ±2%, 250 VDCW.	C256LL*	19A700131P35	Teflon/mica: 35 pF ±2%, 250 VDCW.	L203	19A129774P1	Coil.	W209	19B226733G1	Jumper.			
							C222M*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Deleted in G6 by REV K.	C256L*	19A700131P47	Metallized teflon: 47 pF ±2%, 250 VDCW.	C256L*	19A700131P47	Metallized teflon: 47 pF ±2%, 250 VDCW.	L204	19A701091G1	Coil.	W210	19B226734G1	Jumper.			
	W244	5491689P104	Cable, RF; approx 4 inches long, 350 VOMS, 500 VDC operating voltage.	C211L*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Deleted in G6 by REV K.	C222H*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Deleted in G7 by REV H.	C256L*	19A700131P4													

SYMBOL	GE PART NO.	DESCRIPTION
Z204L*	19A134666P1	Frequency network: selective, 400-500 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:330J:SLAC. Added to G5 by REV L. Added to G9 by REV D.
Z204L*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G6 by REV K.
Z204M*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G7 by REV H.
Z204H*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G8 by REV H.
Z205LL*	19A134666P3	Frequency network: selective, 400-500 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:330J:SLAC. Added to G5 by REV L. Added to G9 by REV D.
Z205L*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G6 by REV K.
Z205M*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G7 by REV H.
Z205H*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G8 by REV H.
Z206*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G5 by REV L. Added to G6 by REV K. Added to G7, G8 by REV H. Added to G9 by REV D.
Z207LL*	19A134666P3	Frequency network: selective, 400-500 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:330J:SLAC. Added to G5 by REV L. Added to G9 by REV D.
Z207L*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G6 by REV K.
Z207M*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G7 by REV H.
Z207H*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G8 by REV H.
Z208LL*	19A134666P3	Frequency network: selective, 400-500 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:330J:SLAC. Added to G5 by REV L. Added to G9 by REV D.
Z208L*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G6 by REV K.
Z208M*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G7 by REV H.
Z208H*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G8 by REV H.
Z209LL*	19A134666P3	Frequency network: selective, 400-500 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:330J:SLAC. Added to G5 by REV L. Added to G9 by REV D.
Z209L*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G6 by REV K.
Z209M*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G7 by REV H.
Z209H*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G8 by REV H.
Z210*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G5 by REV L. Added to G6 by REV K. Added to G7, G8 by REV H. Added to G9 by REV D.
Z211LL*	19A134666P3	Frequency network: selective, 400-500 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:330J:SLAC. Added to G5 by REV L. Added to G9 by REV D.
Z211L*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G6 by REV K.

SYMBOL	GE PART NO.	DESCRIPTION
Z211M*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G7 by REV H.
Z211H*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G8 by REV H.
Z212*	19A134666P1	Frequency network: selective, 470-630 MHz res. freq. 500 VDCW; sim to Dilectron TC501:NPO:240J:SLAC. Added to G5 by REV L. Added to G6 by REV K. Added to G7, G8 by REV H. Added to G9 by REV D.
Z213* and Z214*		NETWORK ASSEMBLY 19A143581G1 (Added to G5 by REV M, G9 by REV E)
L1	19A700024P1	Coil, RF: 100 nH ±10%, 0.08 ohms DC res max, 100 v.
L2	19A701091G2	Coil.
R1	19A700106P15	Composition: 10 ohms ±5%, 1/4 w.
		LOW PASS FILTER 19C327024G1 400-450 MHz (LL) (Added to 19D424895G5 & G36 by REV A) 19C327024G2 450-512 MHz (H) (Added to 19D424895G6-G8 by REV A) 19C327024G7 400-450 MHz (LL) DUPLX (Added to 19D424895G22 & G37 by REV A) (Deleted in 19D424895G22 by REV C, G37 by REV B)
		19C327024G8 450-512 MHz (H) DUPLX (Added to 19D424895G23-G25 by REV A) (Deleted by REV C)
C4290LL	19A700014P4	Metallized teflon: 10 pF ±5%, 250 VDCW.
C4290H	19A700131P9	Metallized teflon: 9 pF ±0.5 pF, 250 VDCW.
C4291LL	19A700131P20	Metallized teflon: 20 pF ±0.5 pF, 100 VDCW.
C4291H	19A700131P18	Metallized teflon: 18 pF ±0.5 pF, 250 VDCW.
C4292LL	19A700131P13	Metallized teflon: 13 pF ±0.5 pF, 250 VDCW.
C4292H	19A700131P12	Teflon: 12 pF ±0.5 pF, 250 VDCW.
C4293	19A700015P37	Teflon/Mica: 220 pF ±5%, 250 VDCW.
L4291LL	19B226709G2	Jumper. (Includes L4292LL).
L4291H	19B226709G1	Jumper. (Includes L4292H).
L4292LL		(Part of L4291LL).
L4292H		(Part of L4291H).
J202 and J203	19A700049P2	Connector, receptacle; 500 VDCW maximum; sim to NTPF-1058.
J206 and J207	19A134263P2	Contact, electrical: sim to Selectro 229-1071.
J208	4033513P4	Contact, electrical: sim to Bead Chain L93-3.
K201	19A700061P1	Hermetic sealed: 180 to 341 ohms coil res, 8-16.3 VDC; sim to GE 38A1V1760A2, CP Clare HPW-1201558, or Potter-Brunfield HCM6160.
W4280 thru W4283		(Part of printed board 19D423812P1).
W4284	19A130607G3	Cable, RF: approx .7 of an inch.

SYMBOL	GE PART NO.	DESCRIPTION
		LOW PASS FILTER MODULE 19C321424G4 (Deleted from 19D424895 by REV A)
C4280H	19A116952P9	Metallized teflon: 9 pF + or 0.5 pF, 250 VDCW.
C4281H	19A116952P18	Metallized teflon: 18 pF + 0.5 pF, 250 VDCW.
C4282H	19A116952P12	Metallized teflon: 12 pF ±0.5 pF, 250 VDCW.
C4283H	19A700015P37	Teflon/Mica: 220 pF ±5%, 250 VDCW.
L4281 and L4282	19B226709G1	Jumper.
J202 and J203	19A130924G1	Connector, receptacle: coaxial, jack type; sim to Cinch 14H11613.
J206 and J207		(Part of K201).
J208	4033513P4	Contact, electrical: sim to Bead Chain L93-3.
K201	19A116722P1	Hermetic sealed: 125 ohms ±20%, 1 form C contact, 9.6 to 15.8 VDC (over the temp range indicated). (Includes J206 & J207).
W4280 thru W4283		(Part of printed board 19D423111P1).
		LOW PASS FILTER-DUPLX W MATCHER 19C327024G1 400-450 MHz (LL) (Added to 19D424895G22 by REV C, G37 by REV B) 19C327024G12 450-512 MHz (H) (Added to 19D424895G23-G25 by REV C)
C4290LL	19A700014P4	Metallized teflon: 10 pF ±5%, 250 VDCW.
C4290H	19A700131P9	Metallized teflon: 9 pF ±0.5 pF, 250 VDCW.
C4291LL	19A700131P20	Metallized teflon: 20 pF ±0.5 pF, 100 VDCW.
C4291H	19A700131P18	Metallized teflon: 18 pF ±0.5 pF, 250 VDCW.
C4292LL	19A700131P13	Metallized teflon: 13 pF ±0.5 pF, 250 VDCW.
C4292H	19A700131P12	Teflon: 12 pF ±0.5 pF, 250 VDCW.
C4293	19A700015P37	Teflon/Mica: 220 pF ±5%, 250 VDCW.
L4291LL	19B226709G2	Jumper. (Includes L4292LL).
L4291H	19B226709G1	Jumper. (Includes L4292H).
L4292LL		(Part of L4291LL).
L4292H		(Part of L4291H).
J202 and J203	19A700049P2	Connector, receptacle; 500 VDCW maximum; sim to NTPF-1058.
J206 and J207	19A134263P2	Contact, electrical: sim to Selectro 229-1071.
J208	4033513P4	Contact, electrical: sim to Bead Chain L93-3.
K201	19A700061P1	Hermetic sealed: 180 to 341 ohms coil res, 8-16.3 VDC; sim to GE 38A1V1760A2, CP Clare HPW-1201558, or Potter-Brunfield HCM6160.
W4280 thru W4283		(Part of printed board 19D423812P1).
W4284	19A130607G3	Cable, RF: approx .7 of an inch.

SYMBOL	GE PART NO.	DESCRIPTION
		ANTENNA MATCHER 19C330778G2
C1B	19A116192P2	Capacitors: 470 pF ±20%, 50 VDCW; sim to Erie 811-A050-W8R-471M.
C2	19A700008P2	Variable: 2.28 to 14.13 pF; sim to EF Johnson 187-0109-005.
C4B	19A700008P1	Variable: 2.04 to 9.9 pF, 250V peak.
CR1	19A700047P3	Silicon: 100 mW; sim to 1N6263.
L1B	19A143342P1	Coil.
R1	19A700106P31	Composition: 47 ohms ±5%, 1/4 w.
		FRAME ASSEMBLY 19D417528G3
W241	5491689P104	Cable, RF: approx 4 inches long, 350 VRMS, 500 VDC operating voltage.
	5492178P2	Washer, spring tension: sim to Wallace Barnes 375-20. (Used with Q202).
	19A702182P1	Spacer. (Used with Q202).
	19A702782P5	Nut, hex, brass: No. 8-32. (Used with Q202).
	N44P9010C6	Machine screw: No. 4-40 x 5/8. (Used with Q203).
	N80P13016C6	Machine screw, Phillips head: No. 6-32 x 1. (Secures Filter Assembly).
	19B201074P306	Tap screw, Phillips POZIDRIV®: No. 6-32 x 3/8. (Secures G4214).
	19C321441P1	Insulator. (Located under 40 watt Module).
	19A701332P4	Insulator, washer: nylon. (Used with Q201).
	N210P9C	Hex nut: No. 4-40. (Secures Q215).
	19A115222P3	Insulator, bushing: (Secures Q215).
	N80P9007C6	Machine screw, Phillips: No. 4-40 x 7/16. (Secures Q215).
	19B201074P308	Tap screw, Phillips POZIDRIV®: No. 6-32 x 1/2. (Secures Filter Board).
	7150186P115	Spacer: No. 6 x 1/2. (Located at junction of W221).
	19B219404G1	Web filter.
	19B201074P312	Tap screw, Phillips POZIDRIV®: No. 6-32 x 3/4. (Secures W221 to spacer).
	19B226212G1	Heat sink. (Center sections-Quantity 3).
	19B226212G3	Heat sink. (Caution nameplate end-Quantity 1).
	19D417513G1	Cover, Heat Sink Assembly.
	7139898P3	Nut, hex, brass: No. 1/4-28. (Secures C297).
	19B201074P204	Tap screw, Phillips POZIDRIV®: No. 4-40 x 1/4. (Secures W241).
	19A134260P1	Cover, Insulator. (Used with Q215).
	4029974P1	Insulator, plate: aluminum. (Located under Q215).
		(Part of printed board 19D432087P2).

PRODUCTION CHANGES

Changes in the equipment to improve performance or to simplify circuits are identified by a "Revision Letter," which is stamped after the model number of the unit. The revision stamped on the unit includes all previous revisions. Refer to the Parts List for descriptions of parts affected by these revisions.

- REV. A - PA Assembly 19D424895G5-G8, G22-G25
To incorporate new low-pass filter. Deleted 19C321424. Added 19C327024.
- REV. A - 40 Watt Module 19C321347G5-G8
To improve power output at cold temperatures. Added CR204 & CR205.
- REV. B - 40 Watt Module 19C321347G5-G8
To improve operation. Deleted C213 and Changed C252LLB. In 19C321347G6: deleted C233L, C257L and added C252LB. In 19C321347G7: deleted C237M and added C232MB. In 19C321347G8: deleted C233H, C257H and added C252HB.
- REV. C - 40 Watt Module 19C321347G5-G8
To improve operation. Deleted C209 and R203. Changed R204.
- REV. D - 40 Watt Module 19C321347G5
To improve operation. Added C209 and R203.
- REV. E - 40 Watt Module 19C321347G5
To improve station operation. Added C213.
- REV. D - 40 Watt Module 19C321347G6-G8
To improve operation. Changed C206.
- REV. F - 40 Watt Module 19C321347G5
To improve operation. Changed C206.
- REV. E - 40 Watt Module 19C321347G7, G8
To improve RF output & efficiency. Changed C237 (Group 8) and C238 (Groups 7 & 8).
- REV. G - 40 Watt Module 19C321347G5
REV. E - 40 Watt Module 19C321347G6
REV. F - 40 Watt Module 19C321347G7, G8
To decrease spurious outputs. Changed C207L, M and C209. Deleted C208L, M, H. Added R203 to Groups 6, 7 and 8.
- REV. H - 40 Watt Module 19C321347G5
To increase output at 406 MHz. Changed C252LLB. Deleted C239. Added C239LLB.
- REV. J - To improve stability. Changed Q203LL.
- REV. F - 40 Watt Module 19C321347G6
To improve stability. Added R216 and C262.
- REV. G - To improve operation. Deleted C262.
- REV. A - 40 Watt Module 19C321347G9
To improve operation. Added C240LL.
- REV. B - To improve stability. Changed Q203LL.
- REV. K - 40 Watt Module 19C321347G5
REV. H - 40 Watt Module 19C321347G6
REV. G - 40 Watt Module 19C321347G7
REV. C - 40 Watt Module 19C321347G8
REV. D - 40 Watt Module 19C321347G9
To incorporate new nomenclature for frequency selection networks.
- REV. A - PA Assembly 19D424895G36, G37
REV. B - PA Assembly 19D424895, G5-G8, G22-G25
To improve operation of power control transistor. Changed Q215.
- REV. C - PA Assembly 19D424895G6
REV. D - PA Assembly 19D424895G9
To improve power output. Added C299.
- REV. C - PA Assembly 19D424895G22-G25
REV. B - PA Assembly 19D424895G27
To improve operation in duplex applications. Changed low pass filters. (Added Antenna Matching Unit).

PARTS LIST

406 - 512 MHz
UNIP ANTENNA MATCHING UNIT
19C330778G2 LOW POWER
19C330778G3 HIGH POWER
ISSUE 1

SYMBOL	GE PART NO.	DESCRIPTION
		----- CAPACITORS -----
C1B	19A116192P2	Ceramic: 470 pF ±20%, 50 VDCW; sim to Erie 8111-A050-W8R-471M.
C2	19A700008P2	Variable, air: 2.28 to 14.13 pF, 250 v; sim to EF Johnson Type T 187-0109-005.
C4B	19A700008P1	Variable, air: 2.04 to 9.9 pF, 250 v; sim to EF Johnson Type T 187-0106-005.
		----- DIODES AND RECTIFIERS -----
CR1	19A700047P3	Diode, silicon: 0.410 volt max.
		----- INDUCTORS -----
L1B	19A143342P1	Coil.
		----- RESISTORS -----
R1	19A700106P31	Composition: 47 ohms ±5%, 1/4 w.

*COMPONENTS ADDED, DELETED OR CHANGED BY PRODUCTION CHANGES